

H5N3004P

Silicon N Channel MOS FET
High Speed Power Switching

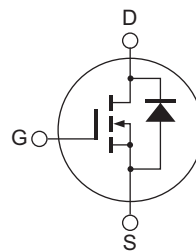
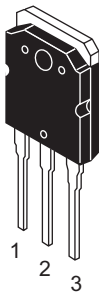
REJ03G1111-0100
(Previous: ADE-208-1523)
Rev.1.00
Sep 07, 2005

Features

- Low on-resistance
- Low leakage current
- High speed switching
- Low gate charge (Qg)
- Avalanche ratings

Outline

RENESAS Package code: PRSS0004ZE-A
(Package name: TO-3P)



1. Gate
2. Drain (Flange)
3. Source

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	300	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	25	A
Drain peak current	I _{D (pulse)} ^{Note 1}	100	A
Body-drain diode reverse drain current	I _{DR}	25	A
Body-drain diode reverse drain peak current	I _{DR (pulse)} ^{Note 1}	100	A
Avalanche current	I _{AP} ^{Note 3}	25	A
Channel dissipation	P _{ch} ^{Note 2}	150	W
Channel to case thermal impedance	θ _{ch-c}	0.833	°C/W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

- Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%
 2. Value at T_c = 25°C
 3. T_{ch} ≤ 150°C

Electrical Characteristics

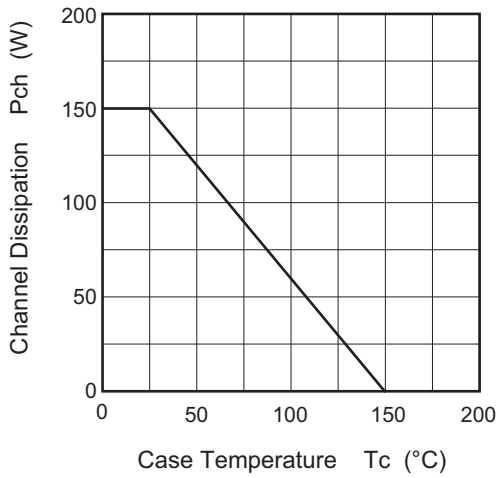
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	300	—	—	V	I _D = 10 mA, V _{GS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	1	μA	V _{DS} = 300 V, V _{GS} = 0
Gate to source leak current	I _{GSS}	—	—	±0.1	μA	V _{GS} = ±30 V, V _{DS} = 0
Gate to source cutoff voltage	V _{GS (off)}	3.0	—	4.0	V	V _{DS} = 10 V, I _D = 1 mA
Forward transfer admittance	y _{fs}	15	25	—	S	I _D = 12.5 A, V _{DS} = 10 V ^{Note 4}
Static drain to source on state resistance	R _{DS (on)}	—	0.076	0.093	Ω	I _D = 12.5 A, V _{GS} = 10 V ^{Note 4}
Input capacitance	C _{iss}	—	3600	—	pF	V _{DS} = 25 V V _{GS} = 0 f = 1 MHz
Output capacitance	C _{oss}	—	400	—	pF	
Reverse transfer capacitance	C _{rss}	—	100	—	pF	
Turn-on delay time	t _{d (on)}	—	50	—	ns	I _D = 12.5 A R _L = 12 Ω V _{GS} = 10 V R _g = 10 Ω
Rise time	t _r	—	120	—	ns	
Turn-off delay time	t _{d (off)}	—	180	—	ns	
Fall time	t _f	—	90	—	ns	
Total gate charge	Q _g	—	110	—	nC	V _{DD} = 240 V V _{GS} = 10 V I _D = 25 A
Gate to source charge	Q _{gs}	—	18	—	nC	
Gate to drain charge	Q _{gd}	—	55	—	nC	
Body-drain diode forward voltage	V _{DF}	—	0.9	1.35	V	I _F = 25 A, V _{GS} = 0
Body-drain diode reverse recovery time	t _{rr}	—	250	—	ns	I _F = 25 A, V _{GS} = 0
Body-drain diode reverse recovery charge	Q _{rr}	—	2.3	—	μC	di _F /dt = 100 A/μs

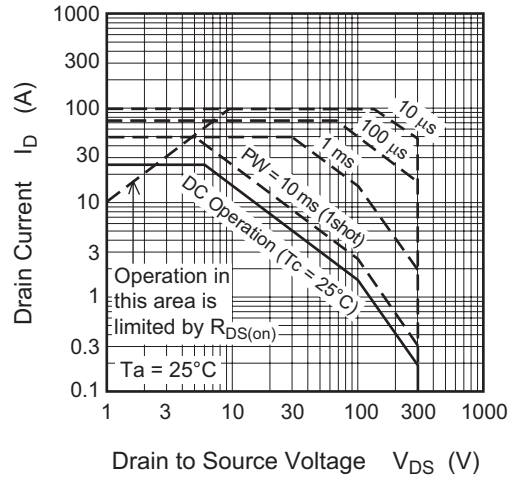
Note: 4. Pulse test

Main Characteristics

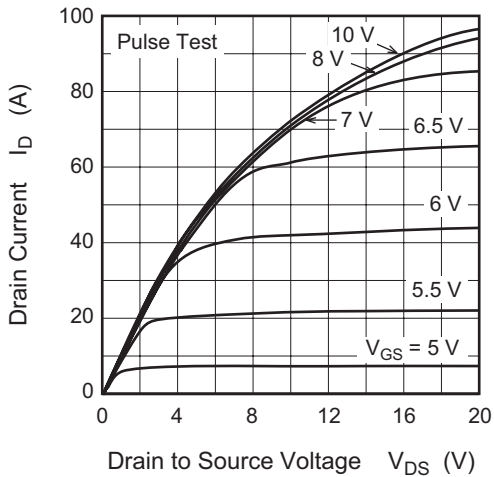
Power vs. Temperature Derating



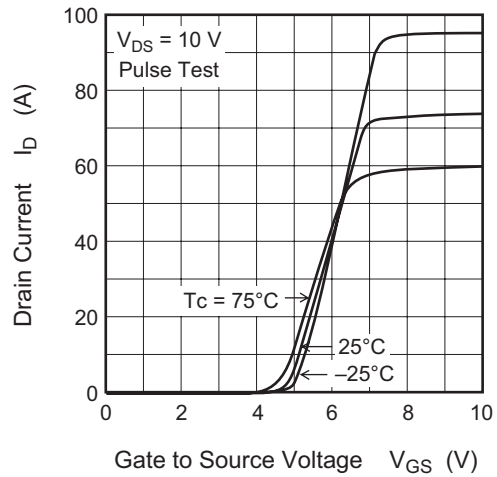
Maximum Safe Operation Area



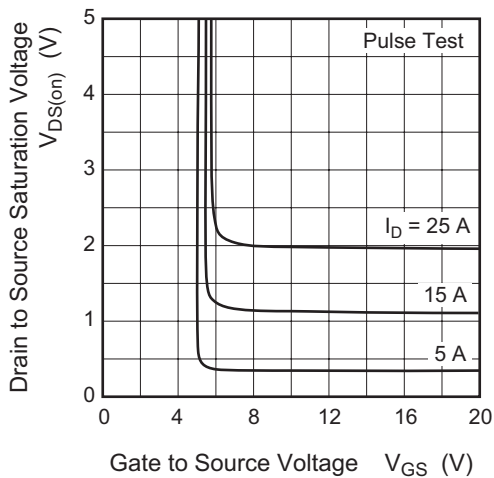
Typical Output Characteristics



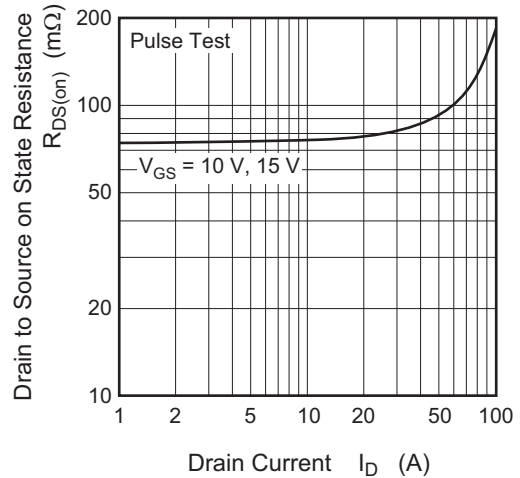
Typical Transfer Characteristics

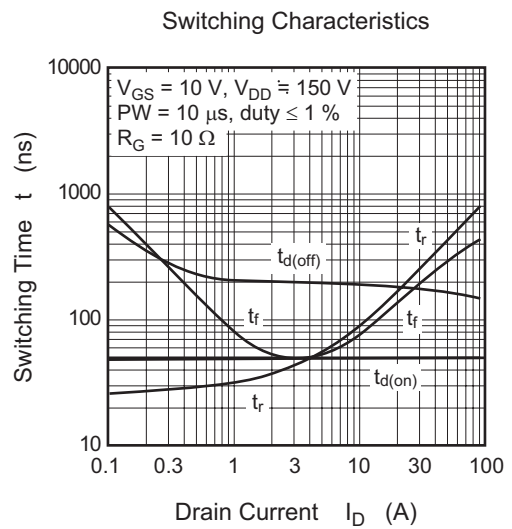
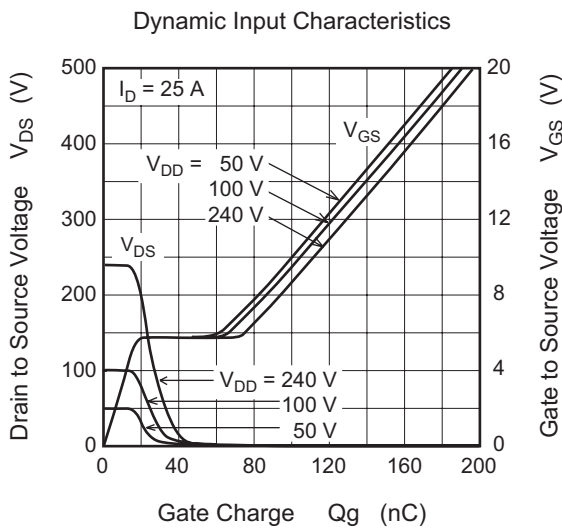
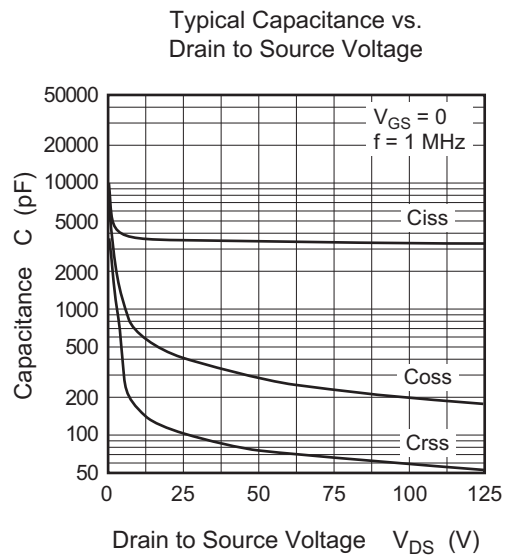
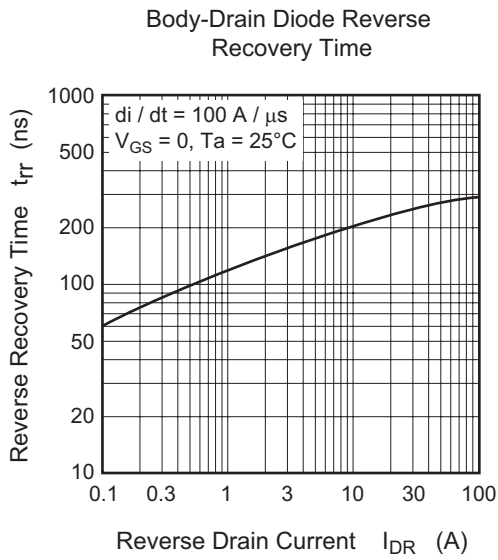
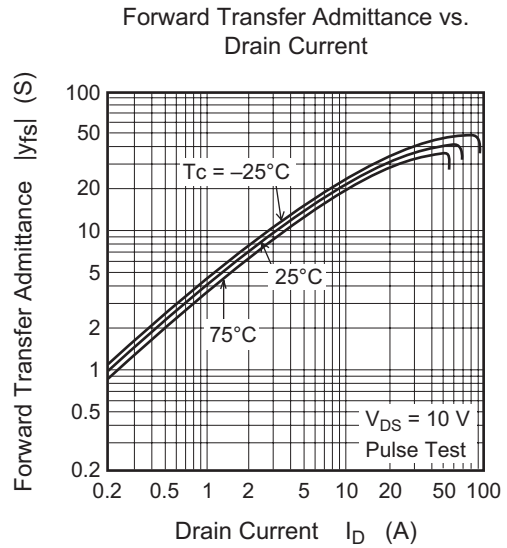
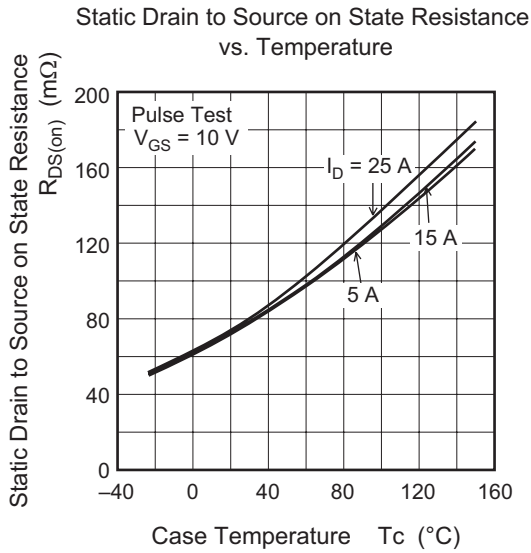


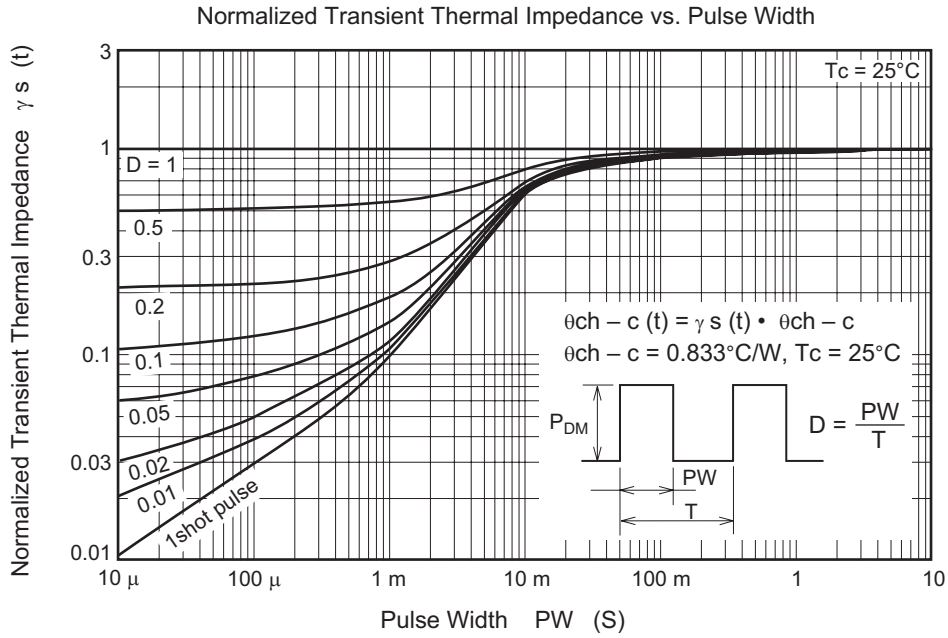
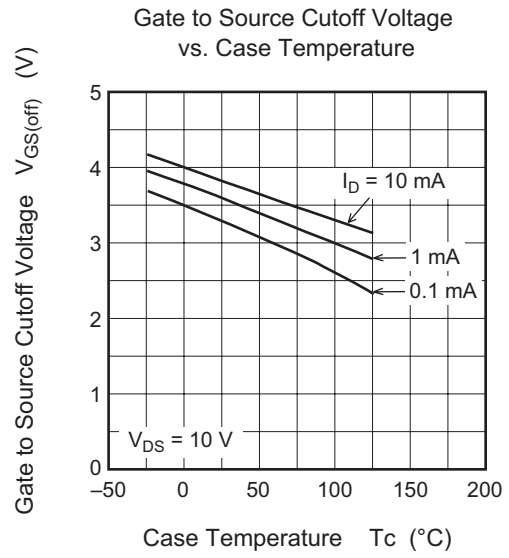
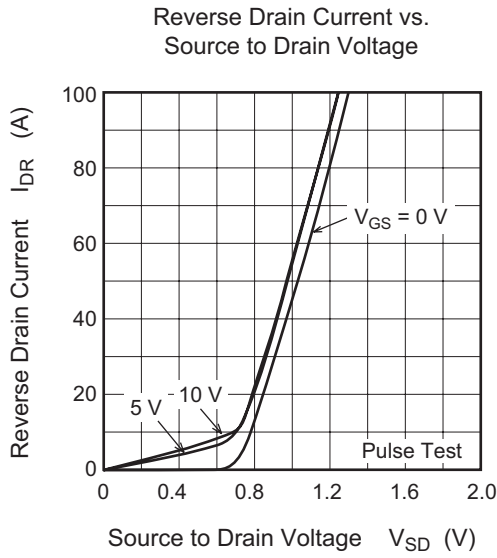
Drain to Source Saturation Voltage vs. Gate to Source Voltage



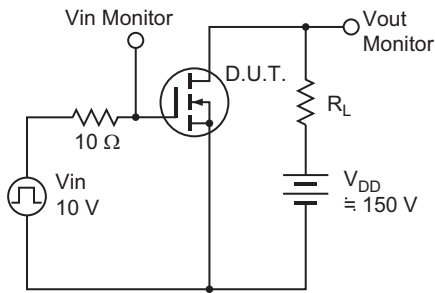
Static Drain to Source on State Resistance vs. Drain Current



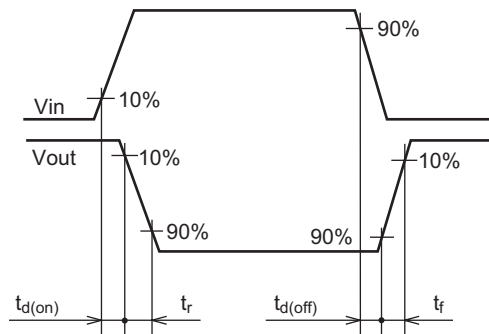




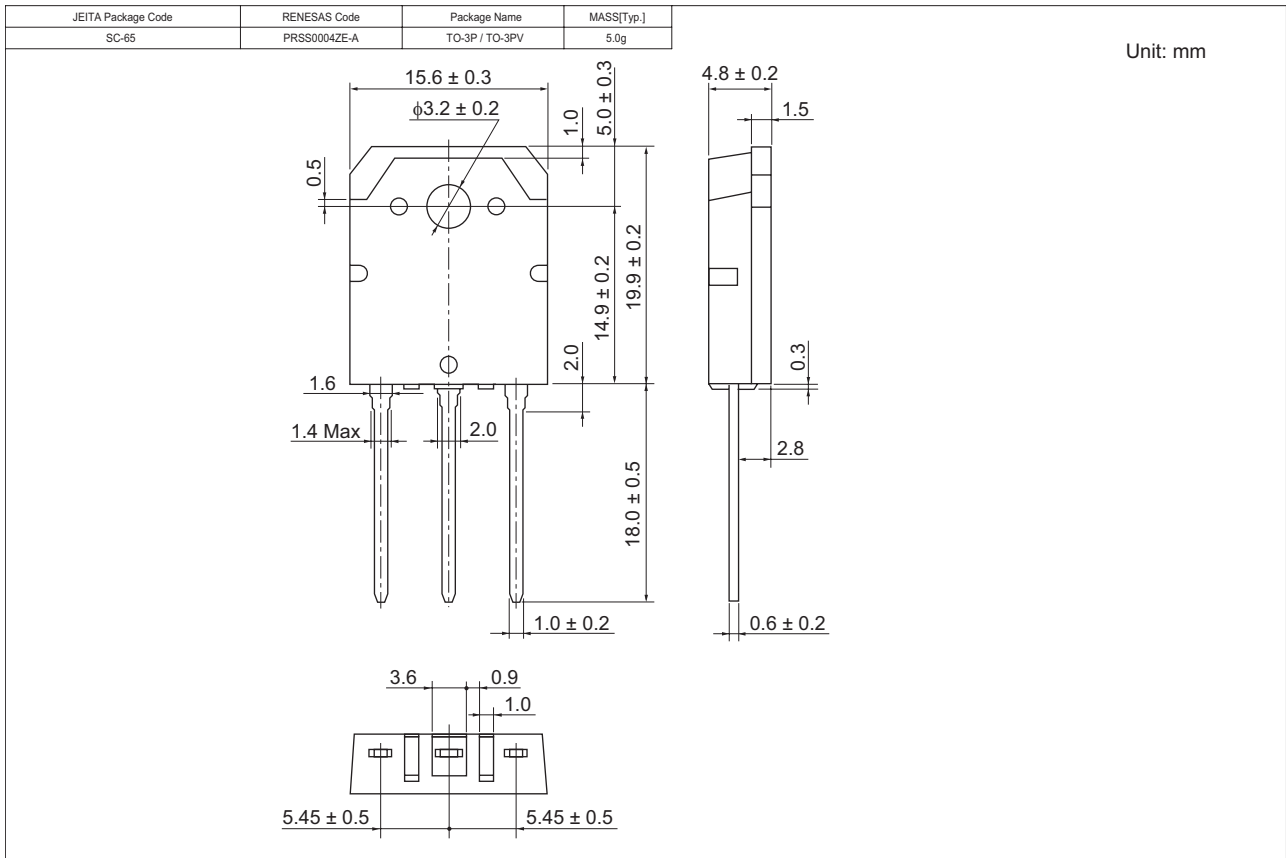
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
H5N3004P-E	360 pcs	Box (Tube)

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510